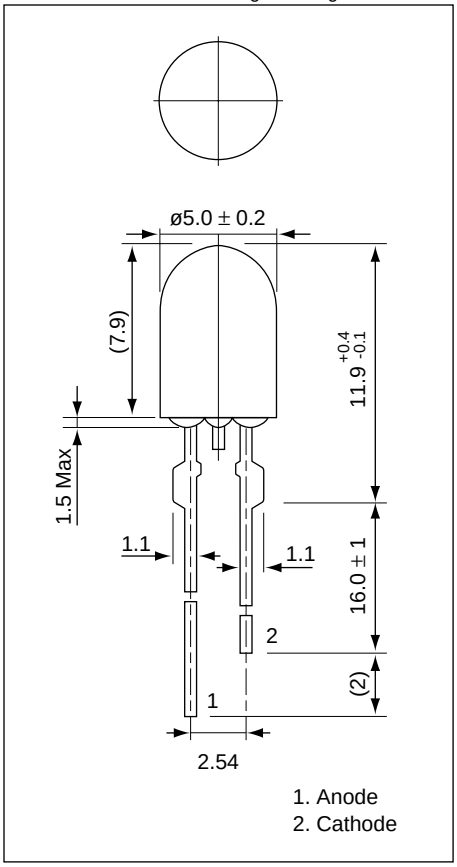
Weight: 0.35 g Unit: mm




# AND256CR

## GaAlAs Red Light Emission

## T-1 3/4 Package (5 mm)

### Features

- Peak wavelength (λp = 660 nm) high brightness emission
- Two chips per lamp
- Low drive current
- Standard T-1 3/4 size
- Fast response time, suitable for pulse drive
- Wide radiation pattern, specially for backlighting

**Maximum Ratings (T = 25°C)**

| Characteristics | Symbol | Rating | Unit |
|---|---|---|---|
| Forward Current | $I_F$ | 30 | mA |
| Reverse Voltage | $V_R$ | 4 | V |
| Power Dissipation | $P_D$ | 140 | mW |
| Operating Temperature Range | $T_{Opr}$ | -30 to 85 | °C |
| Storage Temperature Range | $T_{Stg}$ | -40 to 100 | °C |

**Electro-Optical Characteristics (T = 25°C)**

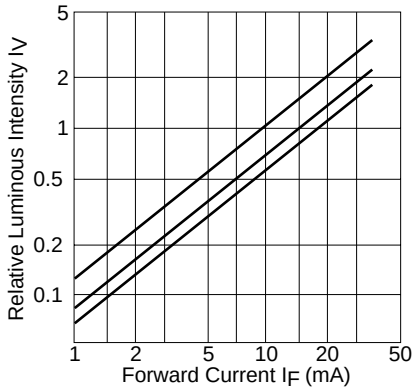
| Characteristics | Symbol | Test Condition | Minimum | Typical | Maximum | Unit |
|---|---|---|---|---|---|---|
| Forward Voltage | $V_F$ | $I_F$ = 20 mA | – | 3.6 | 4.4 | V |
| Reverse Current | $I_R$ | $V_R$ = 4 V | – | – | 100 | µA |
| Luminous Intensity | $I_V$ | $I_F$ = 20 mA | 100 | 350 | – | mcd |
| Peak Emission Wavelength | $I_P$ | $I_F$ = 20 mA | – | 660 | – | nm |
| Spectral Line Half Width | Δλ | $I_F$ = 20 mA | – | 25 | – | nm |
| Dominant Wavelength | λd | $I_F$ = 20 mA | – | 640 | – | nm |
| Full Viewing Angle | θ | $I_V$ = 1/2 Peak | – | 90 | – | degree |

**Precaution**

Please be careful of the following:

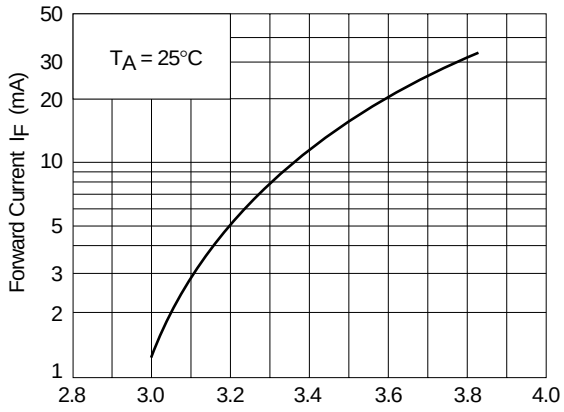
1. Soldering temperature: 260°C max
   Soldering time: 3 sec. max
   Soldering portion of lead: up to 2 mm from the body of the device
2. The lead can be formed up to 5 mm from the body of the device without forming stress.
   Soldering should be performed after the lead forming.

**$I_F$ vs. $V_F$**

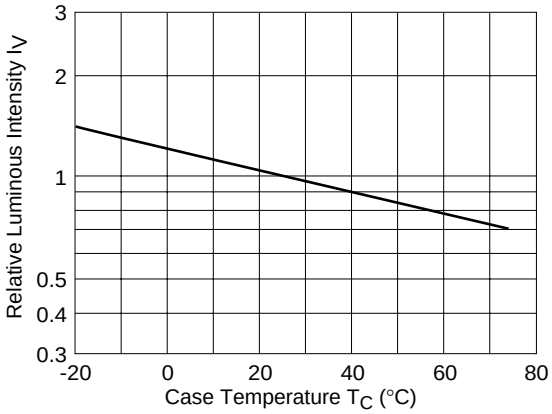



This graph shows relative luminous vs. forward current.
At three points ($I_F$ = 10, 15, 20mA) each relation is normalized.)

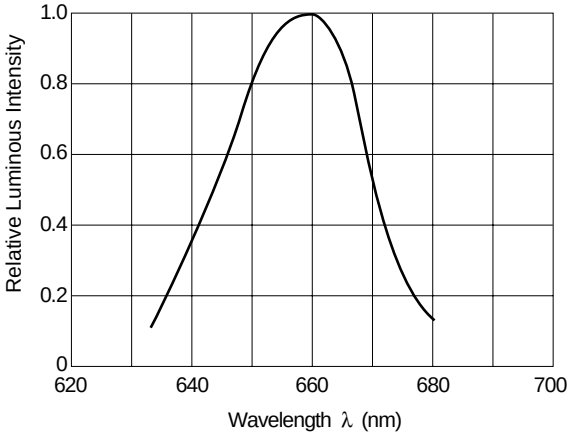
**$I_V$ vs. $V_F$**



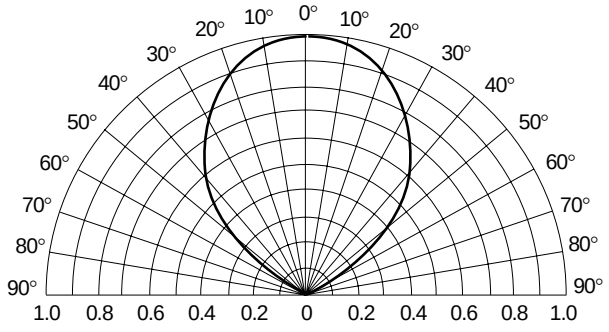

**$I_V$ vs. $T_C$**




**Relative Luminous Intensity – Wavelength**




**Radiation Pattern**




**$I_V$ vs. $T_C$**